

c. **Amendments to Claims**

1 – 7. (canceled)

8. (currently amended) An integrated circuit, comprising:
a substrate having a top surface;
collector, base, and emitter semiconductor layers of a bipolar transistor, the
semiconductor layers forming a vertical sequence on the substrate in which intrinsic portions of
two of the layers are sandwiched between the top surface of the substrate and a remaining top one
of the layers, the base layer comprising an extrinsic portion that laterally encircles a vertical
portion of the top one of the semiconductor layers; and

a dielectric sidewall being interposed between the vertical portion of the top one of the
layers and the extrinsic portion of the base layer; and

wherein the substrate includes a subcollector that forms an electrical contact for the
collector layer, the subcollector being located outside of the portion of the substrate that is
vertically below part of the base layer.

~~wherein the dielectric sidewall has a thickness of 500 to 1500 angstroms.~~

9. (canceled)

10. (previously presented) The integrated circuit of claim 8, wherein the extrinsic portion
of the base layer extends farther away from the substrate than an interface between the top one of
the semiconductor layers and the base layer.

11. (canceled)

12. (previously presented) The integrated circuit of claim 8, wherein a part of the extrinsic
portion of the base layer is located between the substrate and the extrinsic portion of the top one
of the layers.

13. (previously presented) The integrated circuit of claim 12, further comprising a
dielectric layer, a portion of the dielectric layer being located on the extrinsic portion of the base

layer and the extrinsic portion of the top one of the semiconductor layers being located on the dielectric layer.

14. (previously presented) The integrated circuit of claim 12, wherein the extrinsic portion of the base layer extends farther away from the substrate than an interface between the top one of the semiconductor layers and the base layer.

15. (canceled)

16. (previously presented) The integrated circuit of claim 8, wherein the top one of the collector, base, and emitter semiconductor layers is epitaxially grown.

17. (previously presented) The integrated circuit of claim 8, wherein the top one of the collector, base, and emitter semiconductor layers is a graded layer.

18. (previously presented) The integrated circuit of claim 8, wherein the top one of the collector, base, and emitter semiconductor layers includes gallium.

19. (currently amended) The integrated circuit of claim 8, wherein the top one of the collector, base, and emitter semiconductor layers includes indium an InP layer.

20 – 21. (canceled)

22. (currently amended) The integrated circuit of claim 21_12, wherein the dielectric sidewall has a thickness of 500 to 1500 angstroms.

23 – 24. (canceled)

25. (currently amended) The integrated circuit of claim 21_14, further comprising a dielectric layer, a portion of the dielectric layer being located on the part of the extrinsic portion of the base layer and the extrinsic portion of the top one of the semiconductor layers being located on the dielectric layer.

26 – 28. (canceled)

29. (new) The integrated circuit of claim 8, wherein the base layer comprises gallium.

30. (new) The integrated circuit of claim 8, wherein the base layer comprises gallium, indium and arsenic.

31. (new) The integrated circuit of claim 8, wherein the substrate is a InP substrate.